512K x 32 Static RAM

Features

- **High speed**
  - **— t_{AA} = 8, 10, 12 ns**
- **Low active power**
  - **— 1080 mW (max.)**
- **Operating voltages of 3.3 ± 0.3V**
- **2.0V data retention**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{CE}_1$, $\overline{CE}_2$, and $\overline{CE}_3$ features**

Functional Description

The CY7C1062AV33 is a high-performance CMOS Static RAM organized as 524,288 words by 32 bits.

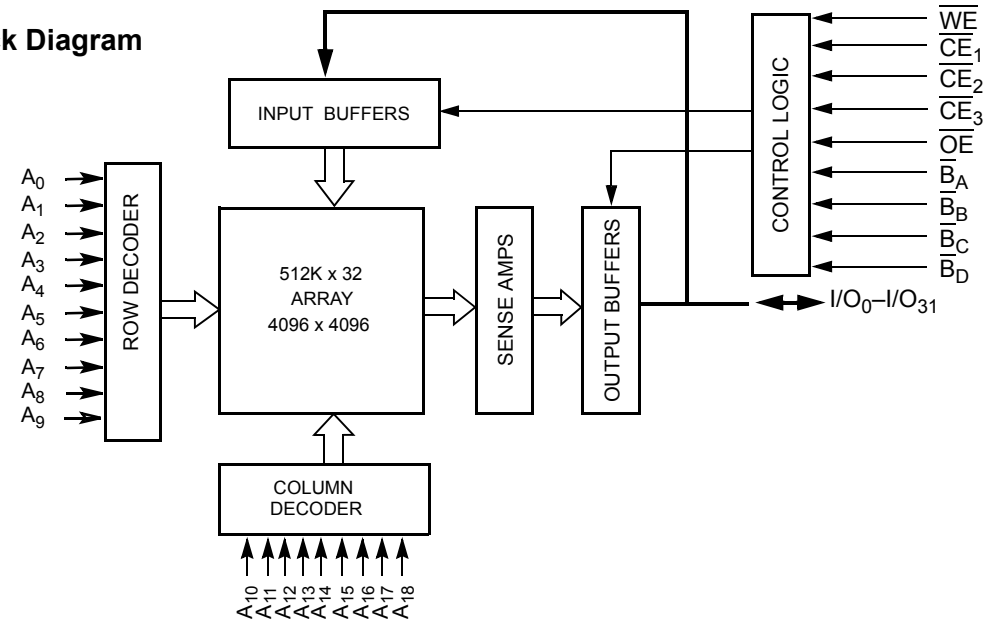
Writing to the device is accomplished by enabling the chip ($\overline{CE}_1$, $\overline{CE}_2$, and $\overline{CE}_3$ LOW) and forcing the Write Enable ($\overline{WE}$) input LOW. If Byte Enable A ($\overline{B}_A$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{18}). If Byte Enable B ($\overline{B}_B$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{18}). Likewise, $\overline{B}_C$ and $\overline{B}_D$ correspond with the I/O pins I/O_{16} to I/O_{23} and I/O_{24} to I/O_{31}, respectively.

Reading from the device is accomplished by enabling the chip ($\overline{CE}_1$, $\overline{CE}_2$, and $\overline{CE}_3$ LOW) while forcing the Output Enable ($\overline{OE}$) LOW and Write Enable ($\overline{WE}$) HIGH. If the first Byte Enable ($\overline{B}_A$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte Enable B ($\overline{B}_B$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. Similarly, $\overline{B}_c$ and $\overline{B}_D$ correspond to the third and fourth bytes. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O_0 through I/O_{31}) are placed in a high-impedance state when the device is deselected ($\overline{CE}_1$, $\overline{CE}_2$or $\overline{CE}_3$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), the byte selects are disabled ($\overline{B}_{A\text{-}D}$ HIGH), or during a write operation ($\overline{CE}_1$, $\overline{CE}_2$, and $\overline{CE}_3$ LOW, and $\overline{WE}$ LOW).

The CY7C1062AV33 is available in a 119-ball pitch ball grid array (PBGA) package.

Logic Block Diagram



Selection Guide

		–8	–10	–12	Unit
Maximum Access Time		8	10	12	ns
Maximum Operating Current	Com'l	300	275	260	mA
	Ind'l	300	275	260	
Maximum CMOS Standby Current	Com'l/Ind'l	50	50	50	mA

Pin Configuration

119-ball PBGA
(Top View)

	1	2	3	4	5	6	7
A	I/O_{16}	A	A	A	A	A	I/O_0
B	I/O_{17}	A	A	$\overline{CE}_1$	A	A	I/O_1
C	I/O_{18}	$\overline{B}_c$	$\overline{CE}_2$	NC	$\overline{CE}_3$	$\overline{B}_a$	I/O_2
D	I/O_{19}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_3
E	I/O_{20}	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	I/O_4
F	I/O_{21}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_5
G	I/O_{22}	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	I/O_6
H	I/O_{23}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_7
J	NC	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	DNU
K	I/O_{24}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_8
L	I/O_{25}	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	I/O_9
M	I/O_{26}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_{10}
N	I/O_{27}	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	I/O_{11}
P	I/O_{28}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	I/O_{12}
R	I/O_{29}	A	$\overline{B}_d$	NC	$\overline{B}_b$	A	I/O_{13}
T	I/O_{30}	A	A	$\overline{WE}$	A	A	I/O_{14}
U	I/O_{31}	A	A	$\overline{OE}$	A	A	I/O_{15}

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[1] .... –0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[1].....–0.5V to V_{CC} + 0.5V

DC Input Voltage[1] .....–0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V
Industrial	–40°C to +85°C	

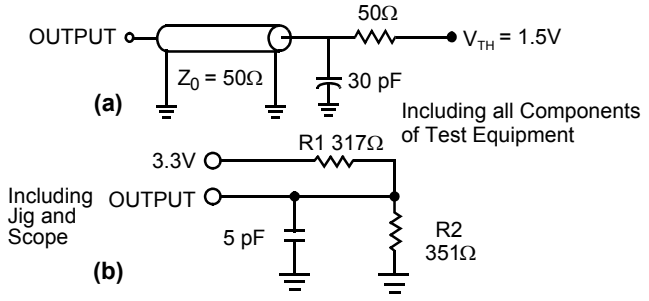
DC Electrical Characteristics Over the Operating Range

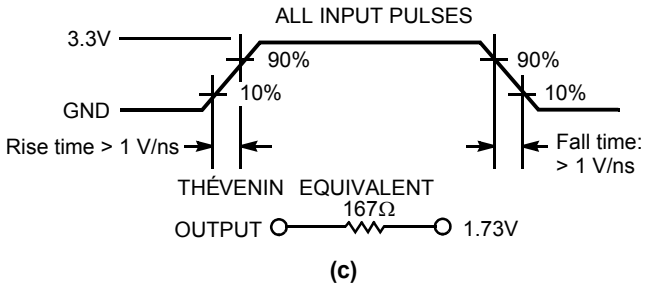
Parameter	Description	Test Conditions		-8 Min.	-8 Max.	-10 Min.	-10 Max.	-12 Min.	-12 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[1]			–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		–1	+1	–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled		–1	+1	–1	+1	–1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = $1/t_{RC}$	Com'l		300		275		260	mA
			Ind'l		300		275		260	mA
I_{SB1}	Automatic CE Power-down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}			70		70		70	mA
I_{SB2}	Automatic CE Power-down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0	Com'l/Ind'l		50		50		50	mA

Capacitance[2]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	8	pF
C_{OUT}	I/O Capacitance		10	pF

AC Test Loads and Waveforms[3]





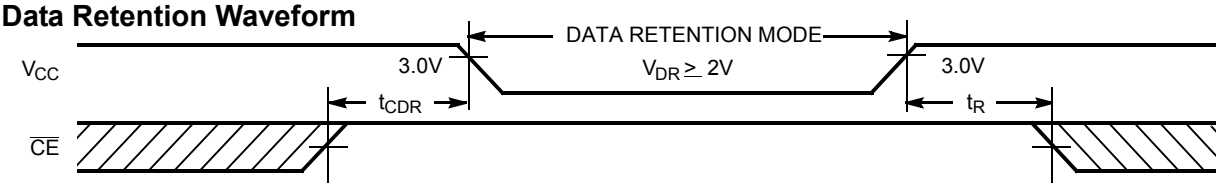
Notes:

1. V_{IL} (min.) = –2.0V for pulse durations of less than 20 ns.
2. Tested initially and after any design or process changes that may affect these parameters.
3. Valid SRAM operation does not occur until the power supplies have reached the minimum operating V_{DD} (3.0V). As soon as 1 ms (T_{power}) after reaching the minimum operating V_{DD}, normal SRAM operation can begin including reduction in V_{DD} to the data retention (V_{CCDR}, 2.0V) voltage.

AC Switching Characteristics Over the Operating Range[4]

Parameter	Description	–8		–10		–12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
t_{power}	V_{CC} (typical) to the first access[5]	1		1		1		ms
t_{RC}	Read Cycle Time	8		10		12		ns
t_{AA}	Address to Data Valid		8		10		12	ns
t_{OHA}	Data Hold from Address Change	3		3		3		ns
t_{ACE}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ LOW to Data Valid		8		10		12	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		5		5		6	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z[6]	1		1		1		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[6]		5		5		6	ns
t_{LZCE}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ LOW to Low-Z[6]	3		3		3		ns
t_{HZCE}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ HIGH to High-Z[6]		5		5		6	ns
t_{PU}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ LOW to Power-up[7]	0		0		0		ns
t_{PD}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ HIGH to Power-down[7]		8		10		12	ns
t_{DBE}	Byte Enable to Data Valid		5		5		6	ns
t_{LZBE}	Byte Enable to Low-Z[6]	1		1		1		ns
t_{HZBE}	Byte Disable to High-Z[6]		5		5		6	ns
Write Cycle[8, 9]								
t_{WC}	Write Cycle Time	8		10		12		ns
t_{SCE}	$\overline{CE}_1$, $\overline{CE}_2$, or $\overline{CE}_3$ LOW to Write End	6		7		8		ns
t_{AW}	Address Set-up to Write End	6		7		8		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	6		7		8		ns
t_{SD}	Data Set-up to Write End	5		5.5		6		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[6]	3		3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[6]		5		5		6	ns
t_{BW}	Byte Enable to End of Write	6		7		8		ns

Data Retention Waveform

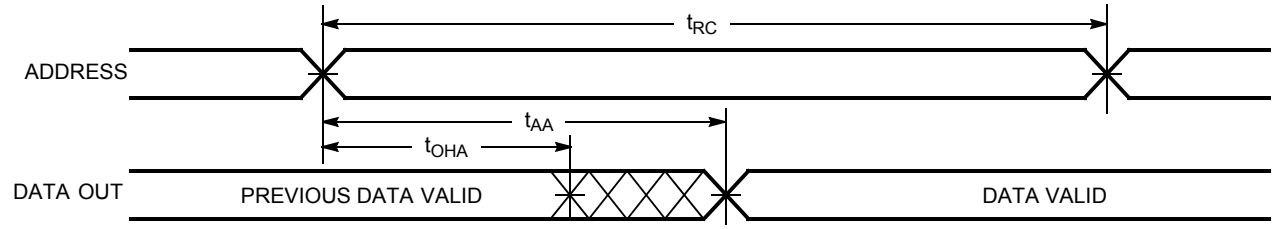


Notes:

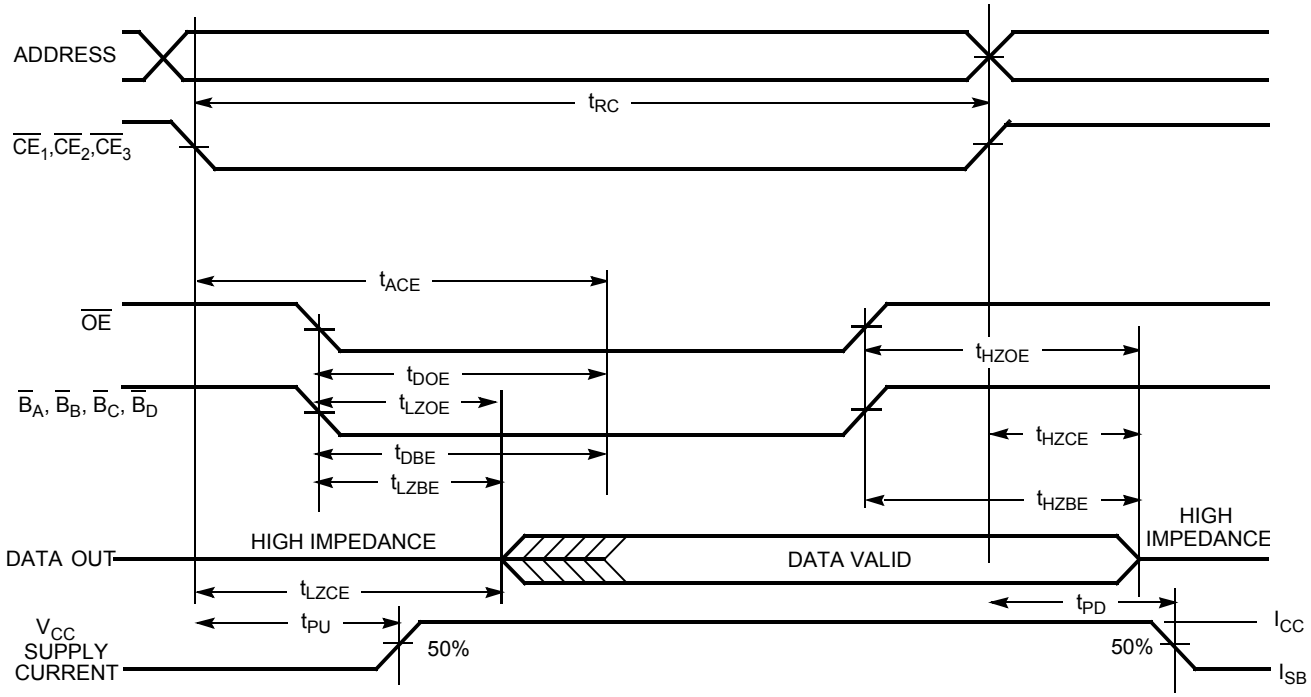
4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and transmission line loads. Test conditions for the read cycle use output loading as shown in (a) of AC Test Loads, unless specified otherwise.
5. This part has a voltage regulator that steps down the voltage from 3V to 2V internally. t_{power} time has to be provided initially before a read/write operation is started.
6. t_{HZOE}, t_{HZCE}, t_{HZWE}, t_{HZBE}, and t_{LZOE}, t_{LZCE}, t_{LZWE}, and t_{LZBE} are specified with a load capacitance of 5 pF as in (b) of AC Test Loads. Transition is measured ± 200 mV from steady-state voltage.
7. These parameters are guaranteed by design and are not tested.
8. The internal write time of the memory is defined by the overlap of $\overline{CE}_1$ LOW, $\overline{CE}_2$ HIGH, $\overline{CE}_3$ LOW, and $\overline{WE}$ LOW. The chip enables must be active and $\overline{WE}$ must be LOW to initiate a write, and the transition of any of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
9. The minimum write cycle time for Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

Read Cycle No. 1[10, 11]



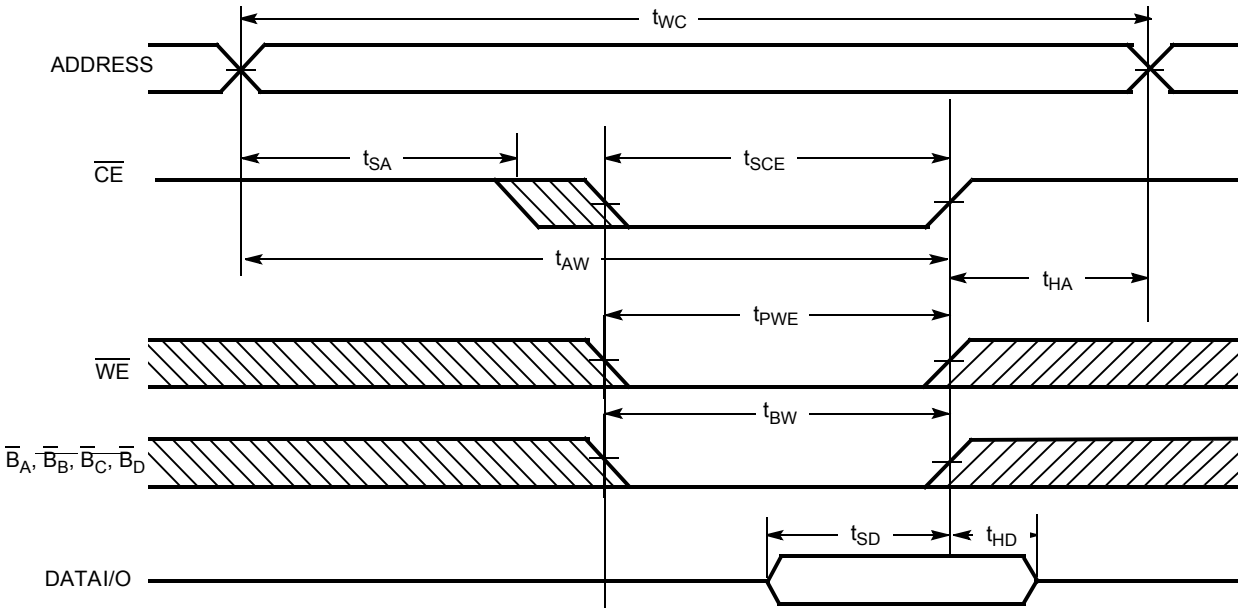
Read Cycle No. 2 ($\overline{OE}$ Controlled)[11, 12]



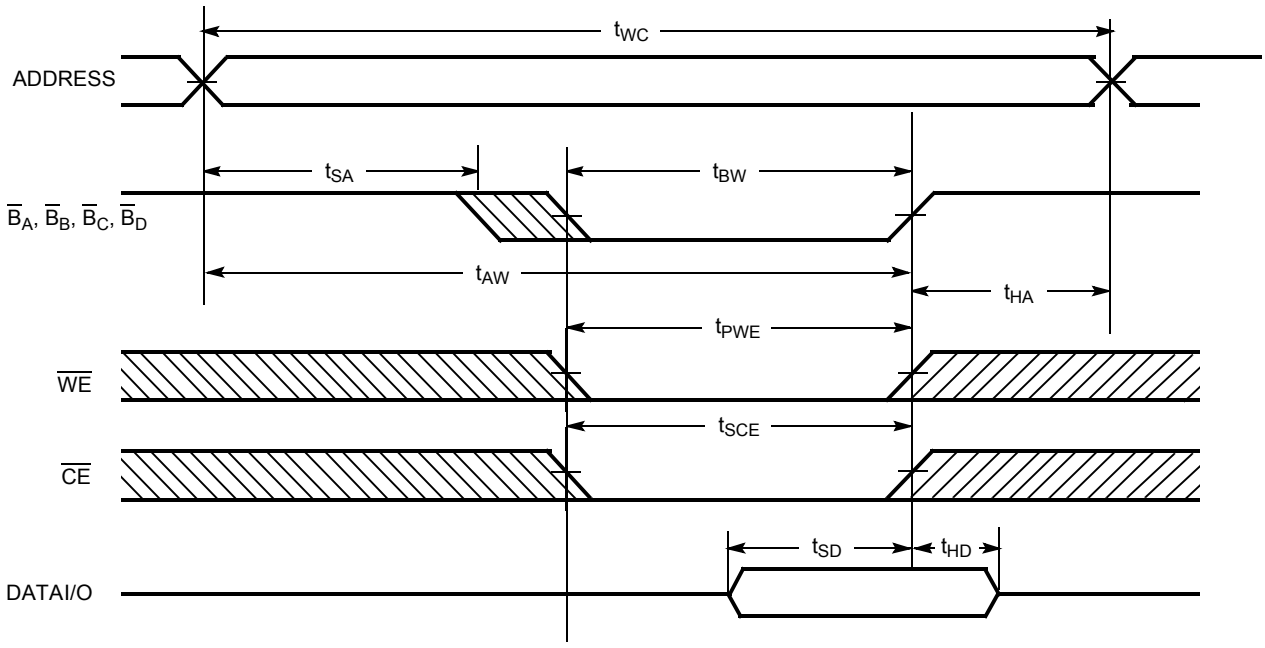
Notes:
10. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{B}_A$, $\overline{B}_B$, $\overline{B}_C$, $\overline{B}_D$ = V_{IL}.
11. $\overline{WE}$ is HIGH for read cycle.
12. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[13, 14, 15]



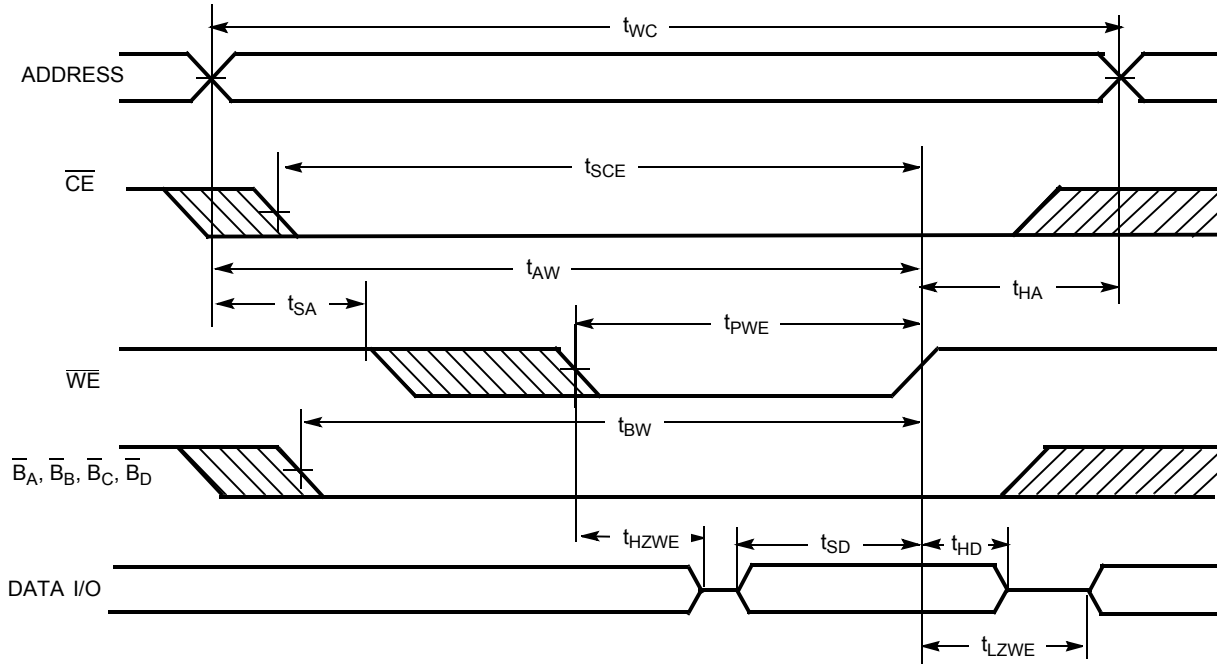
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)[13, 14, 15]



Notes:
13. $\overline{CE}$ indicates a combination of all three chip enables. When ACTIVE LOW, $\overline{CE}$ indicates the $\overline{CE}_1$, $\overline{CE}_2$, and $\overline{CE}_3$ are LOW.
14. Data I/O is high-impedance if $\overline{OE}$ or $\overline{B}_A$, $\overline{B}_B$, $\overline{B}_C$, $\overline{B}_D$ = V_{IH}.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)



Truth Table

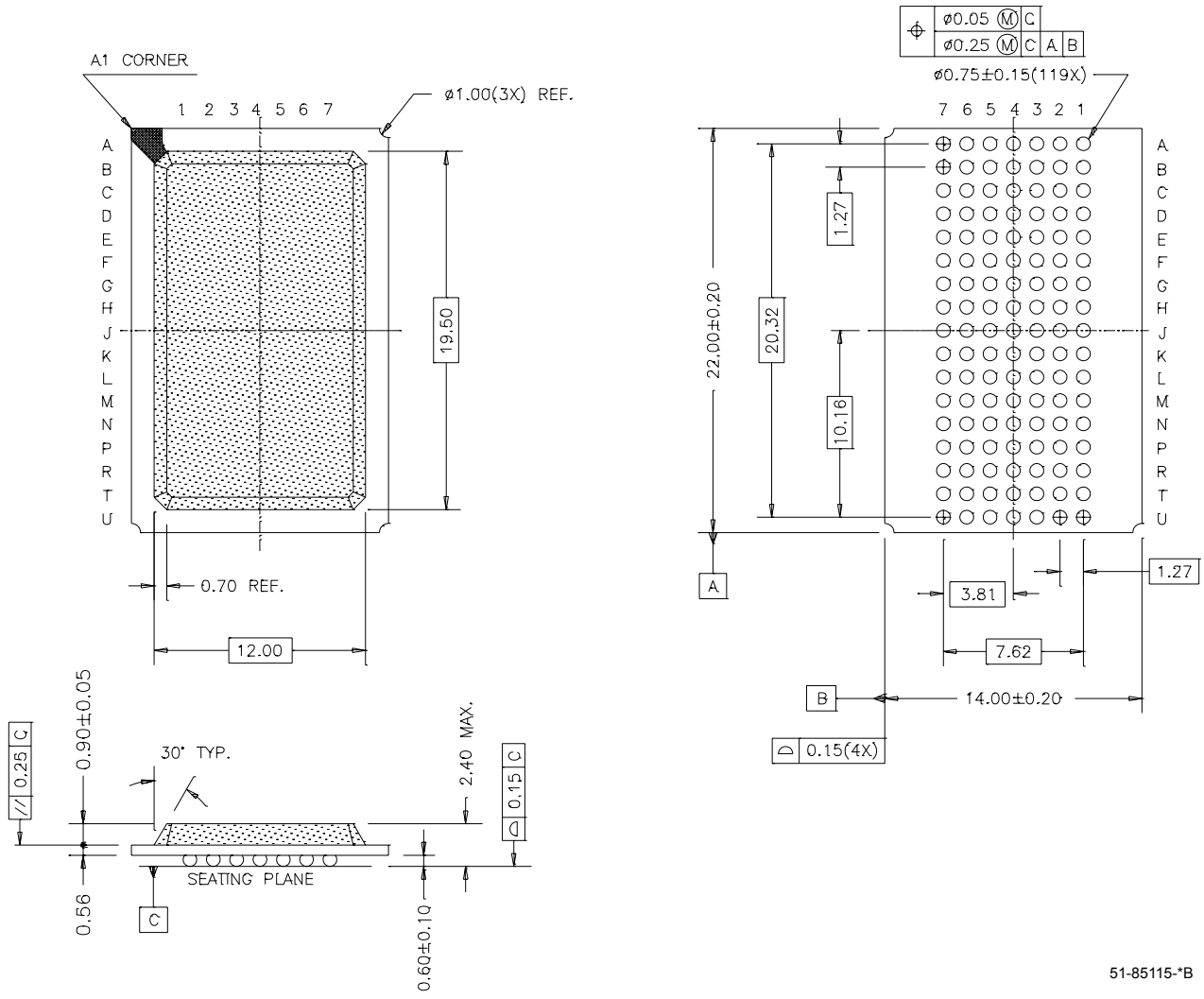
$\overline{CE_1}$	$\overline{CE_2}$	$\overline{CE_3}$	$\overline{OE}$	$\overline{WE}$	$\overline{B_A}$	$\overline{B_B}$	$\overline{B_C}$	$\overline{B_D}$	I/O_0–I/O_7	I/O_8–I/O_{15}	I/O_{16}–I/O_{23}	I/O_{24}–I/O_{31}	Mode	Power
H	X	X	X	X	X	X	X	X	High-Z	High-Z	High-Z	High-Z	Power Down	(I_{SB})
X	H	X	X	X	X	X	X	X	High-Z	High-Z	High-Z	High-Z	Power Down	(I_{SB})
X	X	H	X	X	X	X	X	X	High-Z	High-Z	High-Z	High-Z	Power Down	(I_{SB})
L	L	L	L	H	L	L	L	L	Data Out	Data Out	Data Out	Data Out	Read All Bits	(I_{CC})
L	L	L	L	H	L	H	H	H	Data Out	High-Z	High-Z	High-Z	Read Byte A Bits Only	(I_{CC})
L	L	L	L	H	H	L	H	H	High-Z	Data Out	High-Z	High-Z	Read Byte B Bits Only	(I_{CC})
L	L	L	L	H	H	H	L	H	High-Z	High-Z	Data Out	High-Z	Read Byte C Bits Only	(I_{CC})
L	L	L	L	H	H	H	H	L	High-Z	High-Z	High-Z	Data Out	Read Byte D Bits Only	(I_{CC})
L	L	L	X	L	L	L	L	L	Data In	Data In	Data In	Data In	Write All Bits	(I_{CC})
L	L	L	X	L	L	H	H	H	Data In	High-Z	High-Z	High-Z	Write Byte A Bits Only	(I_{CC})
L	L	L	X	L	H	L	H	H	High-Z	Data In	High-Z	High-Z	Write Byte B Bits Only	(I_{CC})
L	L	L	X	L	H	H	L	H	High-Z	High-Z	Data In	High-Z	Write Byte C Bits Only	(I_{CC})
L	L	L	X	L	H	H	H	L	High-Z	High-Z	High-Z	Data In	Write Byte D Bits Only	(I_{CC})
L	L	L	H	H	X	X	X	X	High-Z	High-Z	High-Z	High-Z	Selected, Outputs Disabled	(I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
8	CY7C1062AV33-8BGC	BG119	14 x 22 mm 119-ball PBGA	Commercial
	CY7C1062AV33-8BGI			Industrial
10	CY7C1062AV33-10BGC			Commercial
	CY7C1062AV33-10BGI			Industrial
12	CY7C1062AV33-12BGC			Commercial
	CY7C1062AV33-12BGI			Industrial

Package Diagram

119-ball PBGA (14 x 22 x 2.4 mm) BG119



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Document History Page

Document Title: CY7C1062AV33 512K x 32 Static RAM Document Number: 38-05137				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	109752	02/27/02	HGK	New Data Sheet
*A	117059	09/19/02	DFP	Removed 15-ns bin and added 8-ns bin. Changed CE_2 TO $\overline{CE}_2$. Changed C_{IN} – input capacitance – from 6 pF to 8 pF. Changed C_{OUT} – output capacitance – from 8 pF to 10 pF.
*B	119389	10/07/02	DFP	Updated I_{CC}, T_{sd}, and T_{doe} parameters. Removed note 7 (I_Z/h_Z comment).
*C	120384	11/13/02	DFP	Final Data Sheet. Removed note 2. Added note 3 to “AC Test Loads and Waveforms” and note 7 to t_{pu} and t_{pd}.
*D	124440	2/25/03	MEG	Changed ISB1 from 100 mA to 70 mA
*E	329638	See ECN	RKF	Removed $\overline{CE}_2$ waveform showing Active High signal timing on Page #5, and included it with the $\overline{CE}_1$, $\overline{CE}_3$ waveform Corrected Truth Table on page 7 with $\overline{CE}_2$ active low information